

# Wide Band GaAs MMIC Amplifier 0.2 - 3.0 GHz

**MAAM02350-A2**

V 2.00

## Features

- High Gain: 18 dB
- Output Power: +14 dBm
- Good Noise Figure: 4 dB
- Single Supply: +6 V
- Gain Flatness:  $\pm 0.75$  dB
- Small, Low Cost 8-Lead Ceramic Package

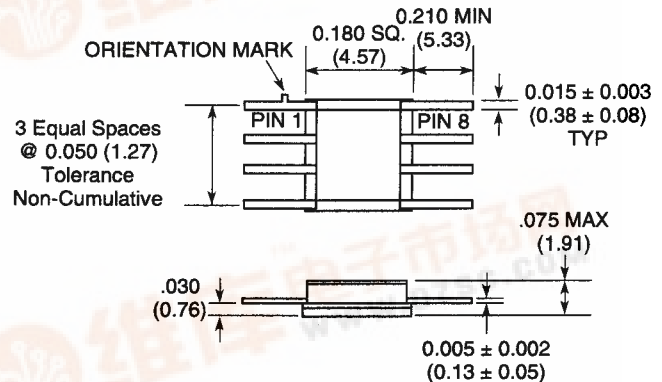
## Description

M/A-COM's MAAM02350-A2 is a wide band, MMIC amplifier housed in a small 8-lead ceramic package. It includes two integrated gain stages and employs resistive feedback to obtain flat gain and a good, 50-ohm, input and output impedance match over a very wide bandwidth. The MAAM02350-A2 operates from a single +6 V supply. It is fully monolithic, requires no external components, and is provided in a low-cost, user-friendly, microwave package.

The MAAM02350-A2 functions well as a generic IF, driver or buffer amplifier where high gain, low noise figure, excellent linearity and low power consumption are important. Because of its wide bandwidth, the MAAM02350-A2 can be used in numerous commercial and government system applications, such as wireless communications, EW and radar.

The MAAM02350-A2 is manufactured in-house using a reliable, 0.5-micron, GaAs MESFET process. This product is 100% RF tested to ensure compliance to performance specifications.

## CR-3



Bottom of case is AC ground.  
Dimensions in ( ) are in mm.  
Unless Otherwise Noted: .xxx =  $\pm 0.010$  (.xx =  $\pm 0.25$ )  
.xx =  $\pm 0.02$  (.x =  $\pm 0.5$ )

## Ordering Information

Part Number	Package
MAAM02350-A2	8-Lead Ceramic
MAAM02350-A2G	Gull Wing

## Electrical Specifications

Test Conditions:  $T_A = +25^\circ\text{C}$ ,  $Z_0 = 50 \Omega$ ,  $V_{DD} = +6 \text{ V}$ ,  $P_{IN} = -30 \text{ dBm}$

Parameter	Units	Min.	Typ.	Max.
Gain	dB	16	18	
Noise Figure	dB		4.0	4.5
Gain Flatness	dB		$\pm 0.5$	
Input VSWR			1.7:1	
Output VSWR			1.3:1	
Output 1 dB Compression	dBm		+14	
Input $IP_3$	dBm		+6	
Reverse Isolation	dB		30	
Bias Current	mA		65	100

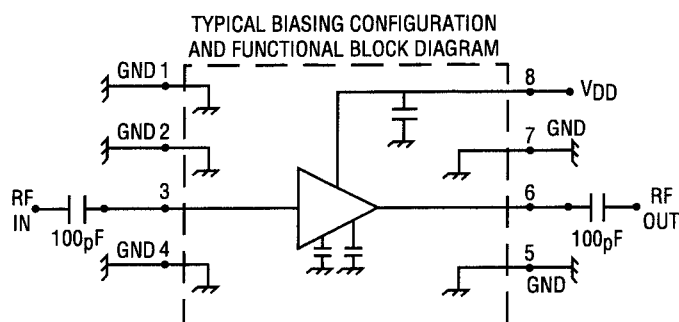
Absolute Maximum Ratings<sup>1</sup>

Parameter	Absolute Maximum
V <sub>DD</sub>	+10 volts
Input Power	+20 dBm
Current	150 mA
Channel Temperature	+150°C
Operating Temperature <sup>2</sup>	-55°C to +100°C
Storage Temperature	-65°C to +150°C

1. Operation of this device outside these limits may cause permanent damage.

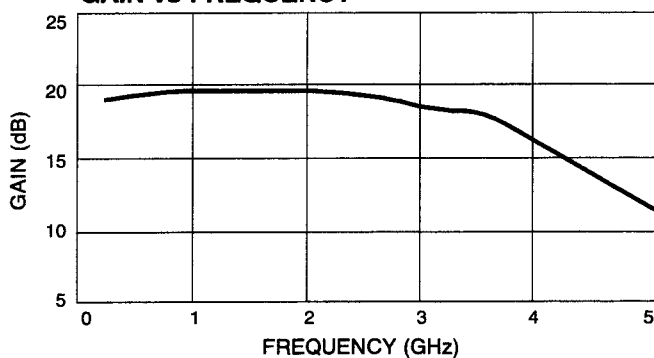
2. Typical thermal resistance ( $\theta_{jc}$ ) = +80°C/W

## Schematic

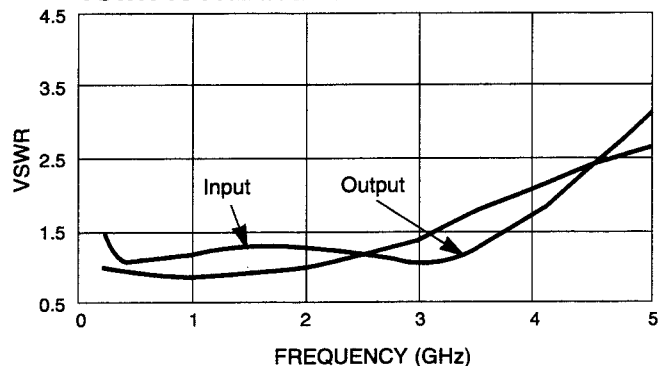


## Typical Performance @ +25°C

GAIN vs FREQUENCY



VSWR vs FREQUENCY



NOISE FIGURE vs FREQUENCY

